

P-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 100	0.042 at $V_{GS} = - 10$ V	- 36	54
	0.047 at $V_{GS} = - 4.5$ V	- 29	

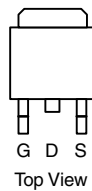
FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

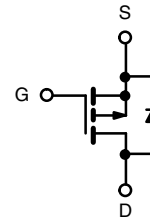


APPLICATIONS

- Load Switch
- ORing

TO-263


Ordering Information:
SUM50P10-42-E3 (Lead (Pb)-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	- 36
		$T_C = 70$ °C	- 30
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	- 40	A
Avalanche Current	I_{AS}	- 40	
Single Avalanche Energy ^a	E_{AS}	80	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	125 ^b
		$T_A = 25$ °C ^c	18.8
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.2	

Notes:

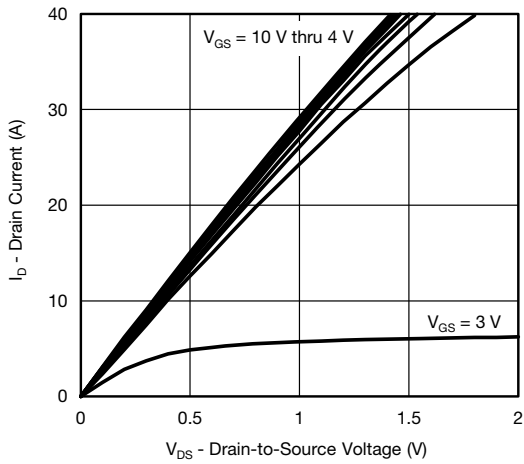
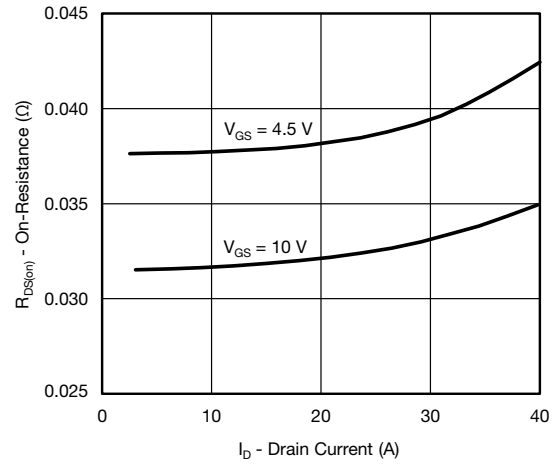
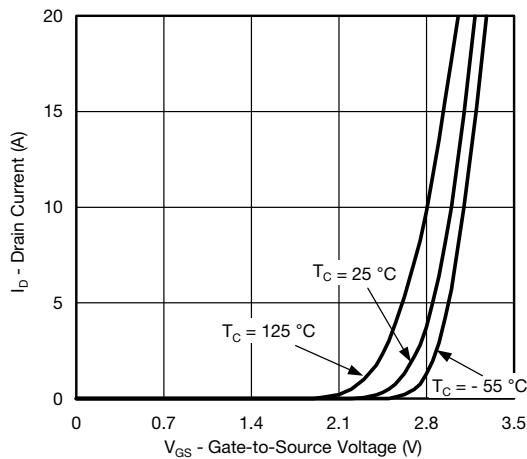
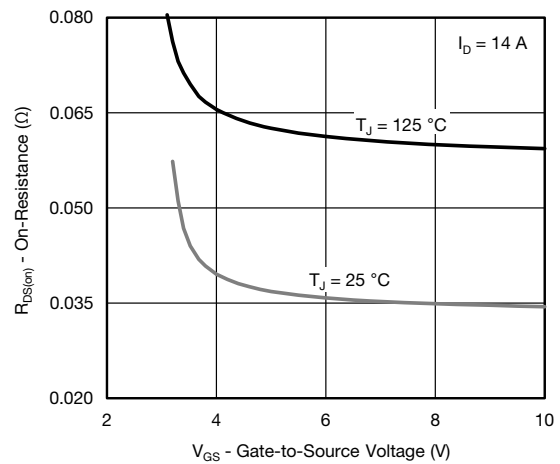
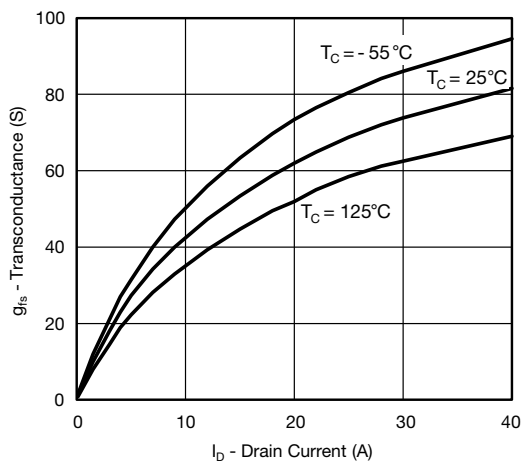
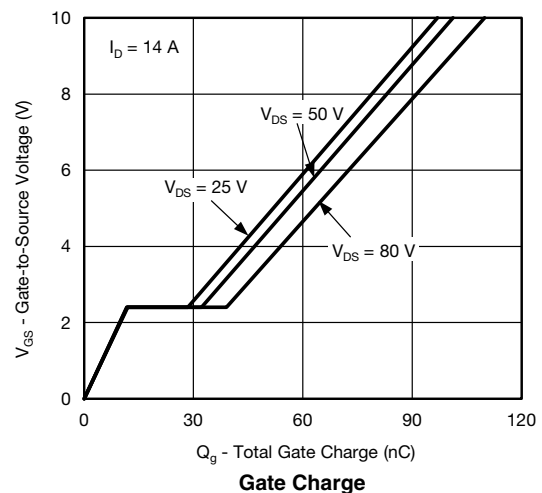
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{DS} = 0, I_D = -250\text{ }\mu\text{A}$	-100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			-50	
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			-250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -10\text{ V}, V_{GS} = -10\text{ V}$	-40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -14\text{ A}$		0.035	0.042	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -13\text{ A}$		0.039	0.047	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -20\text{ V}, I_D = -14\text{ A}$		55		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -50\text{ V}, f = 1\text{ MHz}$		4600		μF
Output Capacitance	C_{oss}			230		
Reverse Transfer Capacitance	C_{rss}			175		
Total Gate Charge ^c	Q_g	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -14\text{ A}$		106	160	nC
				54	81	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -50\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -14\text{ A}$		14		
Gate-Drain Charge ^c	Q_{gd}			26		
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.9	4.6	9.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 5\text{ }\Omega$ $I_D = -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			110	165	
Fall Time	t_f			100	150	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 10\text{ }\Omega$ $I_D = -10\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		42	65	ns
Rise Time	t_r			160	240	
Turn-Off Delay Time	$t_{d(off)}$			100	150	
Fall Time	t_f			100	150	
Drain-Source Body Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}^b$						
Continuous Current	I_S				-36	A
Pulsed Current	I_{SM}				-40	
Forward Voltage ^a	V_{SD}	$I_F = -10\text{ A}, V_{GS} = 0$		-0.8	-1.2	V
Reverse Recovery Time	t_{rr}	$I_F = -10\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$		60	90	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2	3	A
Reverse Recovery Charge	Q_{rr}			150	225	nC

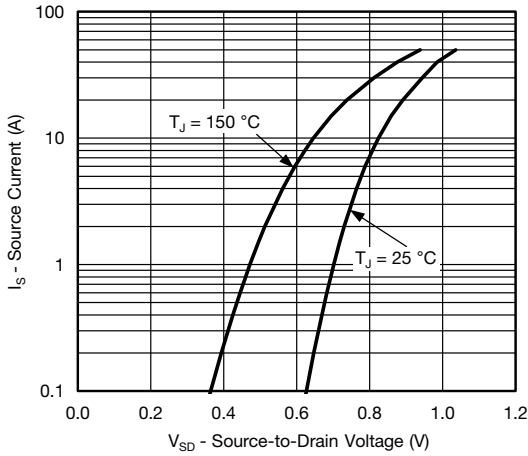
Notes:

- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

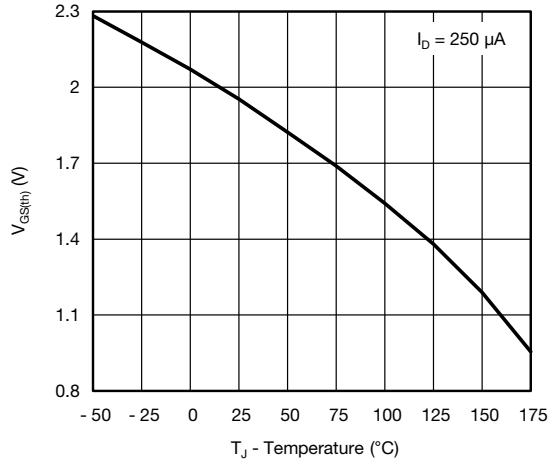
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Drain to Source Voltage vs. I_D

On-Resistance vs. Drain Current

Transfer Characteristics

On-Resistance vs. Gate-to-Source Voltage

Transconductance

Gate Charge

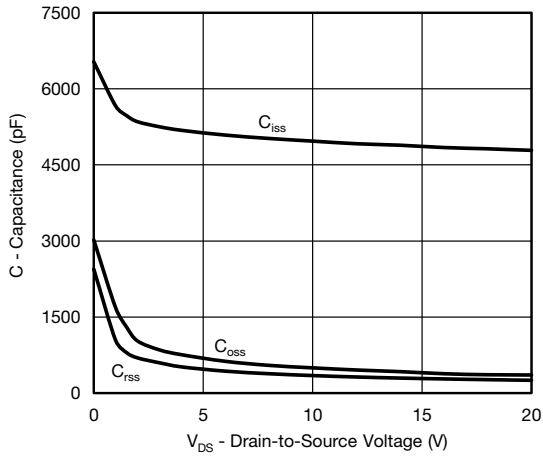
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



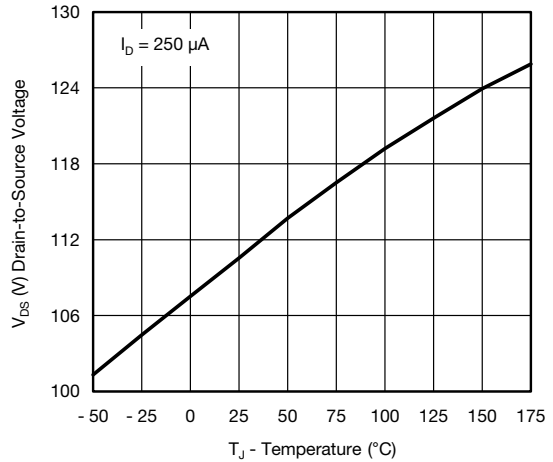
Source-Drain Diode Forward Voltage



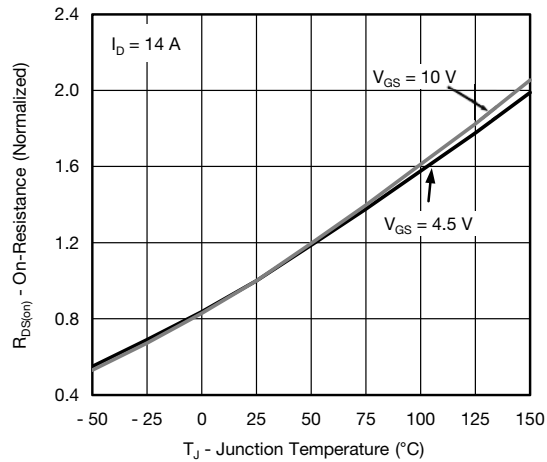
Threshold Voltage



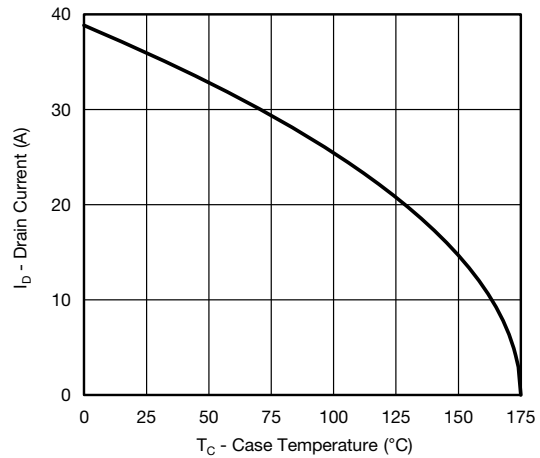
Capacitance



Drain Source Breakdown vs. Junction Temperature

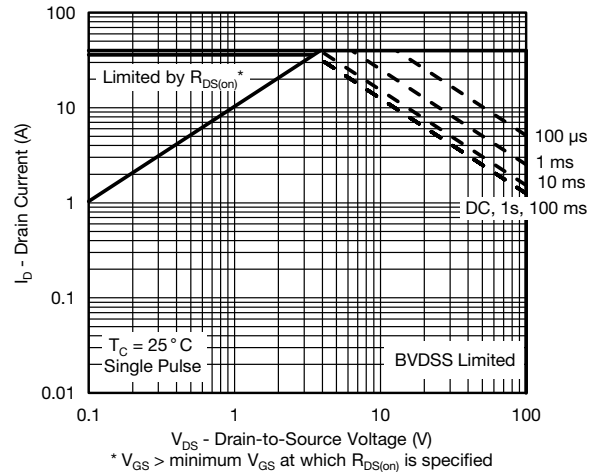
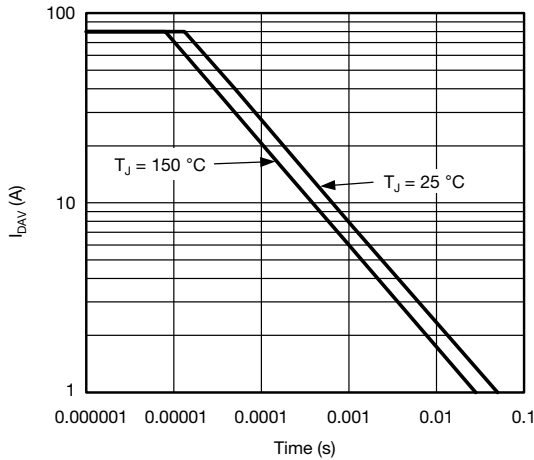


On-Resistance vs. Junction Temperature



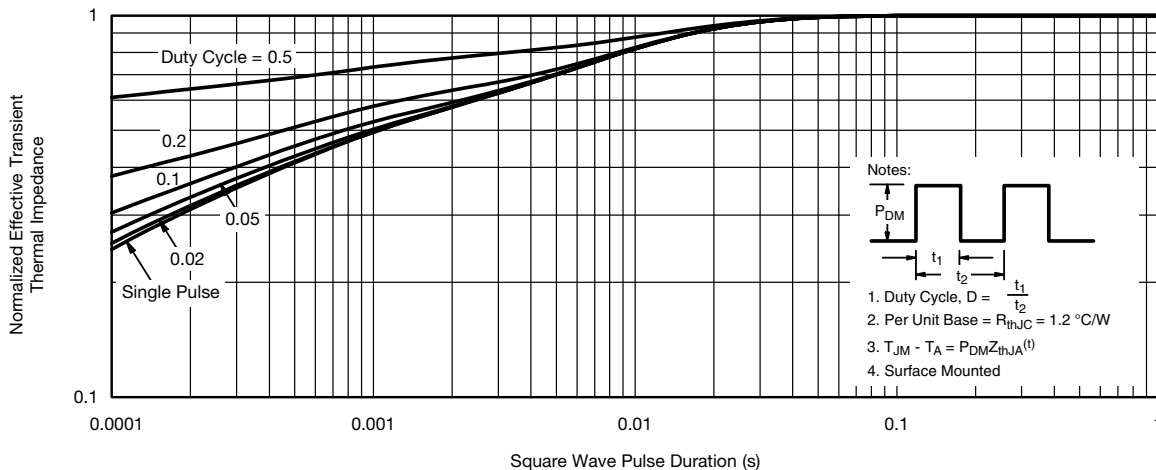
Current Derating

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time

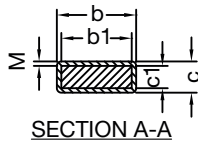
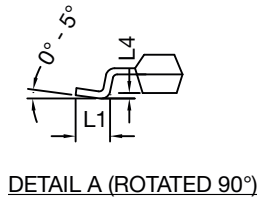
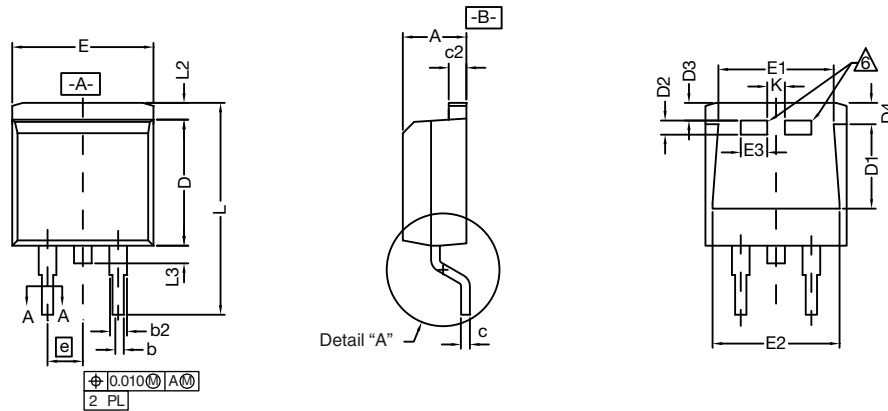
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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TO-263 (D²PAK): 3-LEAD

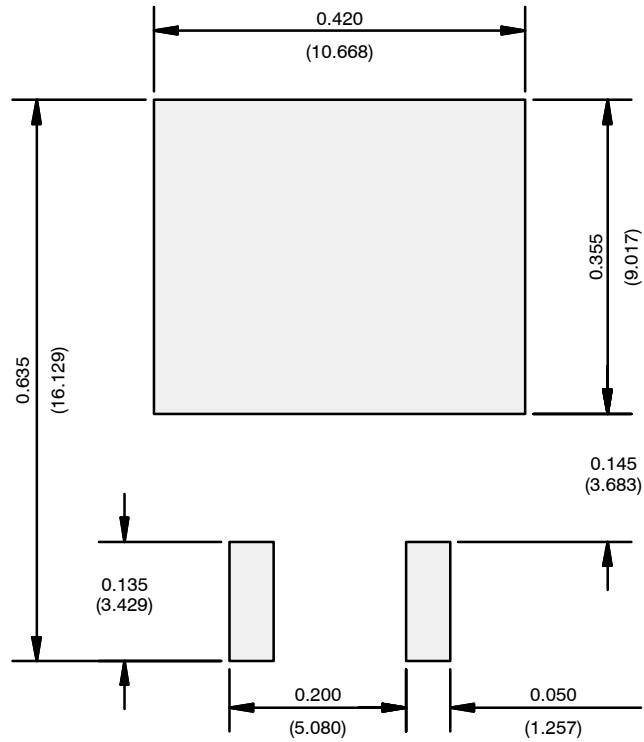


DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
E3	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

Notes

- Plane B includes maximum features of heat sink tab and plastic.
- No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- Pin-to-pin coplanarity max. 4 mils.
- *: Thin lead is for SUB, SYB.
Thick lead is for SUM, SYM, SQM.
- Use inches as the primary measurement.
- This feature is for thick lead.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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